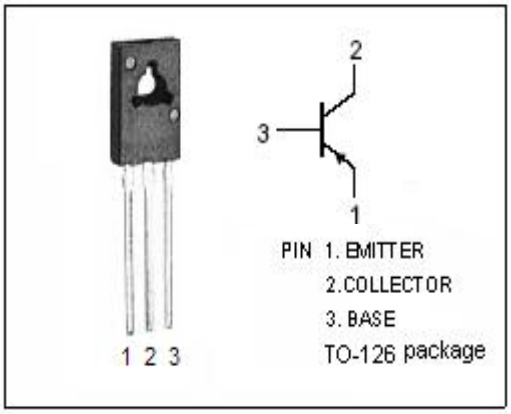
isc Silicon PNP Power Transistor — BD176

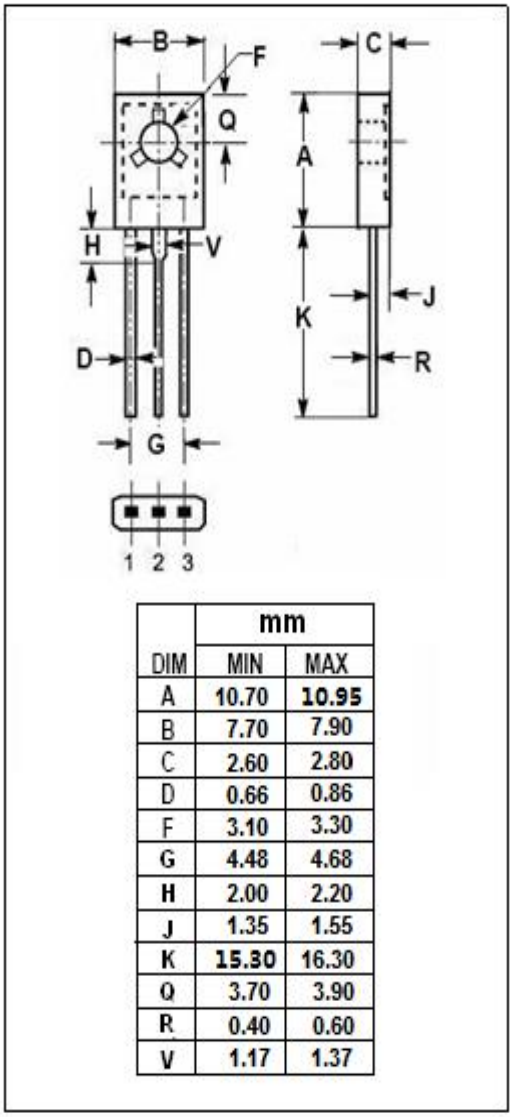
DESCRIPTION

- DC Current Gain-
  : h_{FE}= 40-250(Min)@ I_C= -0.15A
- Collector-Emitter Sustaining Voltage -
  : $V_{CEO(SUS)}$= -45V(Min)
- Complement to type BD175
- Minimum Lot-to-Lot variations for robust device performance and reliable operation



APPLICATIONS

- Designed for medium power linear and switching applications.



DIM	mm MIN	mm MAX
A	10.70	10.95
B	7.70	7.90
C	2.60	2.80
D	0.66	0.86
F	3.10	3.30
G	4.48	4.68
H	2.00	2.20
J	1.35	1.55
K	15.30	16.30
Q	3.70	3.90
R	0.40	0.60
V	1.17	1.37

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-45	V
V_{CEO}	Collector-Emitter Voltage	-45	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current-Continuous	-3	A
I_{CM}	Collector Current-Pulse	-7	A
P_C	Collector Power Dissipation @ T_C=25℃	30	W
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-65~150	℃

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j\text{-}c}$	Thermal Resistance,Junction to Case	8.5	℃/W
$R_{th\ j\text{-}a}$	Thermal Resistance,Junction to Ambient	70	℃/W

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEO(SUS)}$	Collector-Emitter Sustaining Voltage	I_C= -50mA ; I_B= 0	-45			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= -1A; I_B= -0.1A			-0.8	V
$V_{BE(on)}$	Base-Emitter On Voltage	I_C= -1A; V_{CE}= -2V			-1.3	V
I_{CBO}	Collector Cutoff Current	V_{CB}= -45V; I_E= 0			-100	μA
I_{EBO}	Emitter Cutoff Current	V_{EB}= -5V; I_C= 0			-1	mA
h_{FE-1}	DC Current Gain	I_C= -150mA; V_{CE}= -2V	40		250	
h_{FE-2}	DC Current Gain	I_C= -1A; V_{CE}= -2V	15			
f_T	Current-Gain—Bandwidth Product	I_C=- 0.25A; V_{CE}= -10V	3			MHz

◆ **h_{FE-1} Classifications**

6	10	16
40-100	63-160	100-250